# ne<mark>x</mark>peria

#### Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <u>http://www.nxp.com</u>, <u>http://www.philips.com/</u> or <u>http://www.semiconductors.philips.com/</u>, use <u>http://www.nexperia.com</u>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia



# PMBTA42 300 V, 100 mA NPN high-voltage transistor Rev. 05 – 12 December 2008

**Product data sheet** 

# 1. Product profile

#### 1.1 General description

NPN high-voltage transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PMBTA92.

#### **1.2 Features**

High voltage (max. 300 V)

#### 1.3 Applications

Telephony and professional communication equipment

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	300	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		$I_{\rm C} = 1  \rm{mA}$	25	-	-	
		I <sub>C</sub> = 10 mA	40	-	-	
		I <sub>C</sub> = 30 mA	40	-	-	

### 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		3
3	collector		



300 V, 100 mA NPN high-voltage transistor

### 3. Ordering information

Type number <sup>[1]</sup>	Package		
	Name	Description	Version
PMBTA42	-	plastic surface-mounted package; 3 leads	SOT23
PMBTA42/DG			

### 4. Marking

Type number <sup>[1]</sup>	Marking code <sup>[2]</sup>	
PMBTA42	*1D	
PMBTA42/DG	*BV	

- [2] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

# 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	300	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	300	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

#### 300 V, 100 mA NPN high-voltage transistor

# 6. Thermal characteristics

Table 7.

Characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

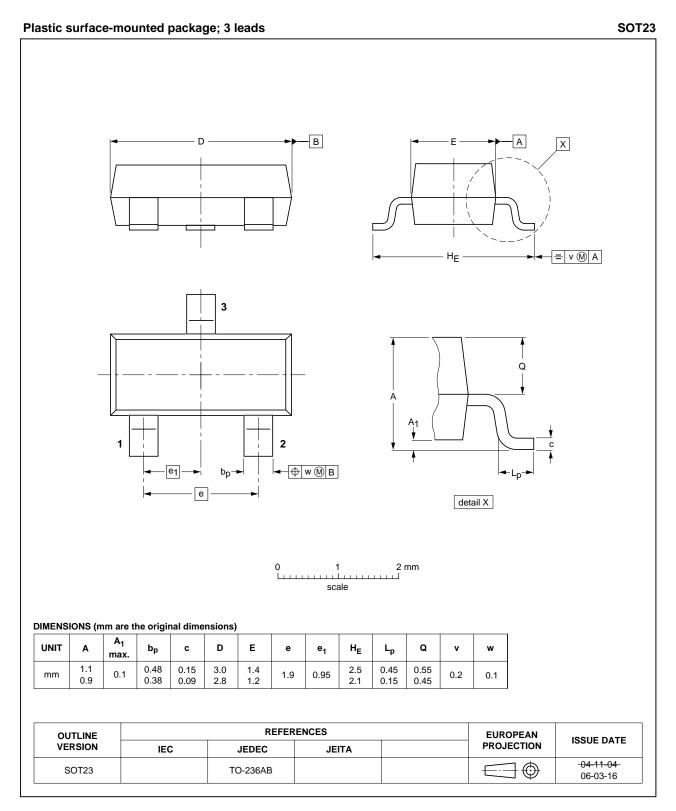
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

# 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 200 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 6 V; I_C = 0 A$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		$I_{\rm C} = 1  \rm{mA}$	25	-	-	
		I <sub>C</sub> = 10 mA	40	-	-	
		I <sub>C</sub> = 30 mA	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C}$ = 20 mA; $I_{\rm B}$ = 2 mA	-	-	500	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{\rm C}$ = 20 mA; $I_{\rm B}$ = 2 mA	-	-	900	mV
C <sub>re</sub>	feedback capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 20 \ V; \ I_{C} = i_{c} = 0 \ A; \\ f = 1 \ MHz \end{array}$	-	-	3	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 20 V; I <sub>C</sub> = 10 mA; f = 100 MHz	50	-	-	MHz

300 V, 100 mA NPN high-voltage transistor

### 8. Package outline



#### Fig 1. Package outline SOT23 (TO-236AB)

#### 300 V, 100 mA NPN high-voltage transistor

### 9. Packing information

#### Table 8. Packing methods

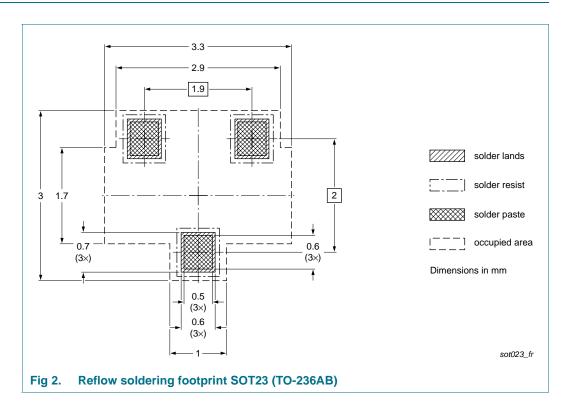
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Package Description		Packing quantity		
				3000	10000	
PMBTA42	SOT23	4 mm pitch, 8 mm tape and reel		-215	-235	
PMBTA42/DG						

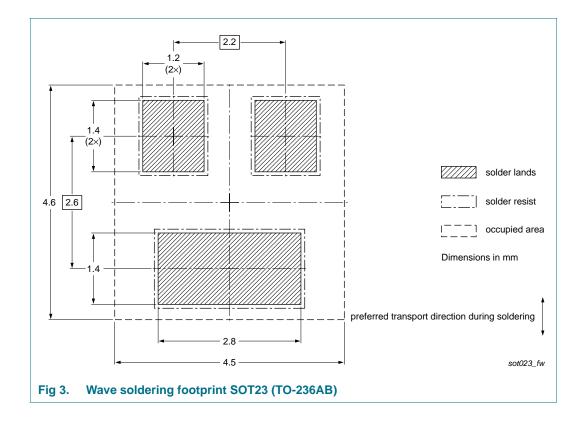
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

[2] /DG: halogen-free

# 10. Soldering



#### 300 V, 100 mA NPN high-voltage transistor



#### 300 V, 100 mA NPN high-voltage transistor

# 11. Revision history

Table 9. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA42_5	20081212	Product data sheet	-	PMBTA42_4
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the n	ew company name whe	ere appropriate.
	<ul> <li>Type numb</li> </ul>	er PMBTA42/DG added		
	Table 4 "Ma	urking codes": enhanced		
	Section 12	"Legal information": updated	t	
PMBTA42_4	20040122	Product specification	-	PMBTA42_3
PMBTA42 3	19990422	Product specification	-	PMBTA42 43 CNV 2

#### 300 V, 100 mA NPN high-voltage transistor

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### 12.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

#### 12.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

#### 12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

### 13. Contact information

For more information, please visit: <u>http://www.nxp.com</u>

For sales office addresses, please send an email to: salesaddresses@nxp.com

#### 300 V, 100 mA NPN high-voltage transistor

#### 14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	1
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	3
8	Package outline	4
9	Packing information	5
10	Soldering	5
11	Revision history	7
12	Legal information	8
12.1	Data sheet status	8
12.2	Definitions	8
12.3	Disclaimers	8
12.4	Trademarks	8
13	Contact information	8
14	Contents	9

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2008.

All rights reserved.



Date of release: 12 December 2008 Document identifier: PMBTA42\_5



# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Nexperia manufacturer:

Other Similar products are found below :

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM 2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13 NTE15 NTE16001